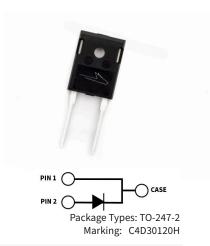


### 4th Generation 1200 V, 30 A Silicon Carbide Schottky Diode

### **Description**

With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.



#### **Features**

- Low Forward Voltage (V<sub>F</sub>) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior

### **Applications**

- Industrial Switched Mode Power Supplies
- Uninterruptible & AUX Power Supplies
- Boost for PFC & DC-DC Stages
- Solar Inverters

# **Maximum Ratings** ( $T_c = 25^{\circ}$ C Unless Otherwise Specified)

| Parameter                                | Symbol           | Value | Unit | Test Conditions   | Notes  |  |
|--|------------------|-------|------|---|--------|--|
| Repetitive Peak Reverse Voltage          | V <sub>RRM</sub> | 1200  | V    |   |        |  |
| DC Blocking Voltage                      | V <sub>DC</sub>  | 1200  | V    |   |        |  |
|  |                  | 94    |      | T <sub>c</sub> = 25 °C  |        |  |
| Continuous Forward Current               | I <sub>F</sub>   | 45    | A    | T <sub>c</sub> = 135 °C   | Fig. 3 |  |
|  |                  | 30    |      | T <sub>c</sub> = 155 °C   |        |  |
| Repetitive Peak Forward Surge<br>Current | I <sub>FRM</sub> | 121   |      | T <sub>c</sub> = 25 °C, t <sub>p</sub> = 10 ms, Half Sine Wave      |        |  |
|  |                  | 68    |      | $T_c = 110  ^{\circ}\text{C}, t_p = 10  \text{ms}, Half Sine Wave}$ |        |  |
| Non-Repetitive Forward Surge<br>Current  | I <sub>FSM</sub> | 233   |      | T <sub>c</sub> = 25 °C, t <sub>p</sub> = 10 ms, Half Sine Wave      | Fig. 8 |  |
|  |                  | 209   |      | $T_c = 110  ^{\circ}\text{C}, t_p = 10  \text{ms}, Half Sine Wave}$ |        |  |
| i²t Value                                | ∫i²t             | 271   |      | $T_{c} = 25 ^{\circ}\text{C}, t_{p} = 10 \text{ms}$                 |        |  |
|  |                  | 218   |      | $T_c = 110 {}^{\circ}\text{C}, t_p = 10 \text{ms}$                  |        |  |
| Power Dissipation                        | P <sub>tot</sub> | 441   | W    | T <sub>c</sub> = 25 °C  | Fig. 4 |  |
|  |                  | 191   |      | T <sub>c</sub> = 110 °C   |        |  |

### **Electrical Characteristics**

| Parameter                 | Symbol         | Тур. | Max. | Unit | Test Conditions   | Notes  |  |
|---------------------------|----------------|------|------|------|---|--------|--|
| Forward Voltage           | , v            | 1.5  | 1.8  | V    | I <sub>F</sub> = 30 A, T <sub>i</sub> = 25 °C                 | Fig. 1 |  |
|                           | V <sub>F</sub> | 2.2  | 3    |      | I <sub>F</sub> = 30 A, T <sub>j</sub> = 175 °C                | Fig. 1 |  |
| Reverse Current           |                | 40   | 250  |      | $V_R = 1200 \text{ V}, T_j = 25 \text{ °C}$                   | Fig. 2 |  |
| Reverse current           | l R            | 70   | 450  | μΑ   | $V_R = 1200 \text{ V}, T_j = 175 \text{ °C}$                  | Fig. 2 |  |
| Total Capacitive Charge   | Q <sub>c</sub> | 152  |      | nC   | $V_R = 800 \text{ V}, T_j = 25 \text{ °C}$                    | Fig. 5 |  |
|                           |                | 2177 |      |      | $V_R = 0 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$   |        |  |
| Total Capacitance         | С              | 136  |      | pF   | $V_R = 400 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$ | Fig. 6 |  |
|                           |                | 100  |      |      | $V_R = 800 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$ |        |  |
| Capacitance Stored Energy | E <sub>c</sub> | 44   |      | μJ   | V <sub>R</sub> = 800 V  | Fig. 7 |  |

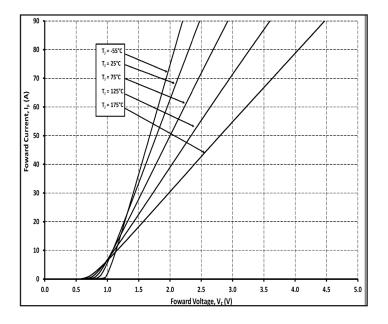
Notes:

SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

#### **Thermal & Mechanical Characteristics**

| Parameter                                      | Symbol                   | Value       | Unit   | Notes      |
|--|--------------------------|-------------|--------|------------|
| Thermal Resistance, Junction to Case (Typical) | R <sub>0, JC (TYP)</sub> | 0.34        | °C/W   |            |
| Junction Temperature                           | T <sub>j</sub>           | -55 to +175 | - °C   |            |
| Case & Storage Temperature                     | T <sub>c</sub>           | -55 to +150 |        |            |
| TO 247 Manuatina Tanana                        |                          | 1           | Nm     | M3 Screw   |
| TO-247 Mounting Torque                         | -                        | 8.8         | lbf-in | 6-32 Screw |

# **Typical Performance**



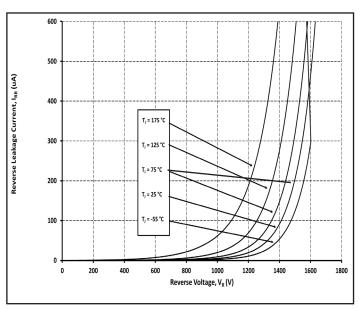
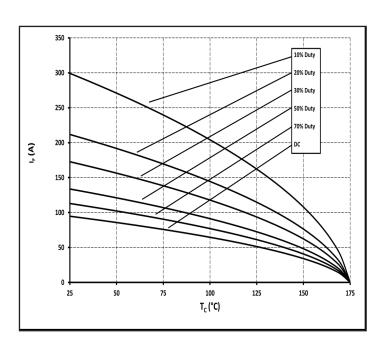


Figure 1. Forward Characteristics

**Figure 2. Reverse Characteristics** 



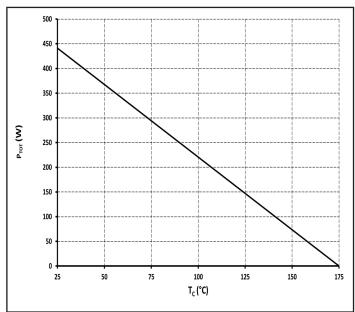
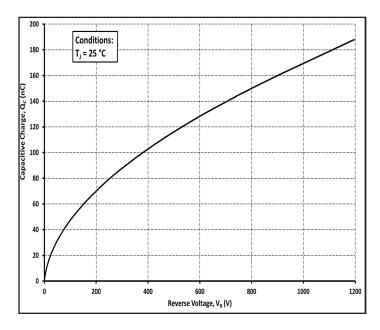


Figure 3. Current Derating

Figure 4. Power Derating

# **Typical Performance**



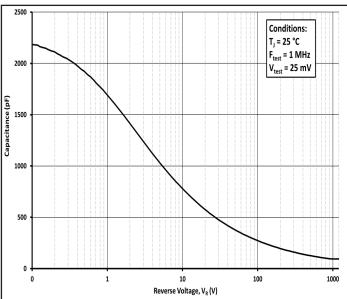
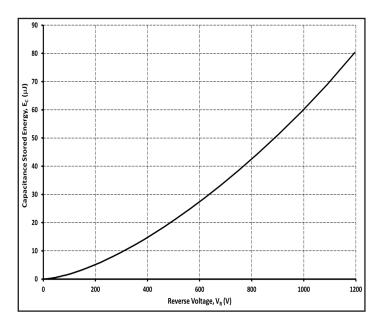


Figure 5.
Total Capacitance Charge vs. Reverse Voltage

Figure 6.
Capacitance vs. Reverse Voltage



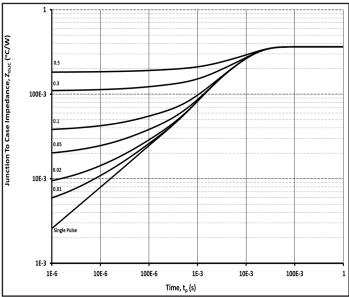
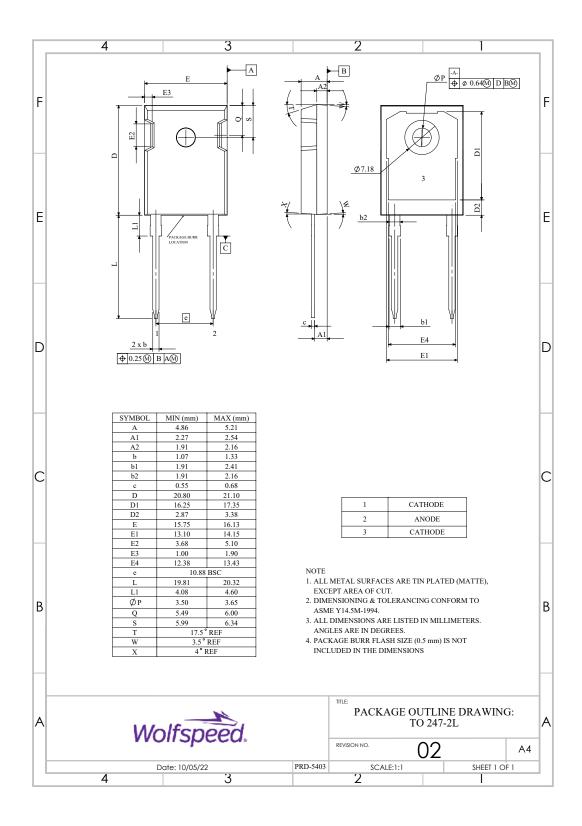


Figure 7.
Typical Capacitance Stored Energy

**Figure 8. Transiant Thermal Impedence** 

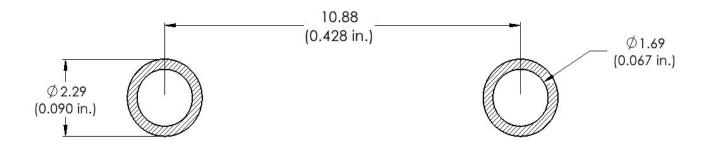
### **Package Dimensions & Pin-Out**

Package: TO-247-2 ( All dimensions are in mm)



# **Recommended Solder Pad Layout**

( All dimensions are in mm)



# **Product Ordering Information**

| Order Number | Packing Type |
|--------------|--------------|
| C4D30120H    | Tube         |

REACh, RoHS, and Halogen-Free compliance documentation available for this product.

# **Revision History**

| Document Version | Date of Release | Description of changes      |
|------------------|-----------------|-----------------------------|
| 0                | January - 2019  | Initial Release             |
| 1                | January - 2023  | Updated POD and Landing Pad |

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